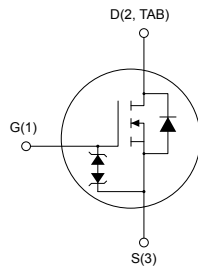
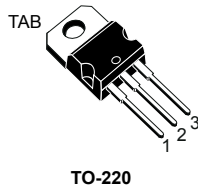


## N-channel 600 V, 0.175 $\Omega$ typ., 18 A MDmesh™ M2 EP Power MOSFET in a TO-220 package



### Features

Order code	$V_{DS}$ at $T_J$ max.	$R_{DS(on)}$ max.	$I_D$
STP25N60M2-EP	650 V	0.188 $\Omega$	18 A

- Extremely low gate charge
- Excellent output capacitance ( $C_{OSS}$ ) profile
- Very low turn-off switching losses
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications
- Tailored for Very high frequency converters ( $f > 150$  kHz)

### Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 enhanced performance (EP) technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance, optimized switching characteristics with very low turn-off switching losses, rendering it suitable for the most demanding very high frequency converters.

#### Product status link

[STP25N60M2-EP](#)

#### Product summary

<b>Order code</b>	STP25N60M2-EP
<b>Marking</b>	25N60M2EP
<b>Package</b>	TO-220
<b>Packing</b>	Tube

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	18	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	11.3	A
$I_{DM}^{(1)}$	Drain current (pulsed)	72	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

1. Pulse width limited by safe operating area.
2.  $I_{SD} \leq 18\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS\ peak} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$ .
3.  $V_{DS} \leq 480\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.83	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	$^\circ\text{C}/\text{W}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	3.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	200	mJ

## 2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	600			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_C = 125\text{ }^\circ\text{C}^{(1)}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$		0.175	0.188	$\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance		-	1090	-	pF
$C_{oss}$	Output capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	56	-	pF
$C_{rss}$	Reverse transfer capacitance		-	1.6	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}, V_{GS} = 0\text{ V}$	-	255	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0\text{ A}$	-	7	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 18\text{ A},$ $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 15. Test circuit for gate charge behavior)	-	29	-	nC
$Q_{gs}$	Gate-source charge		-	6	-	nC
$Q_{gd}$	Gate-drain charge		-	12	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching energy**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{(off)}$	Turn-off energy (from 90% $V_{GS}$ to 0% $I_D$ )	$V_{DD} = 400\text{ V}, I_D = 2\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$	-	7	-	$\mu\text{J}$
		$V_{DD} = 400\text{ V}, I_D = 4\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$	-	8	-	$\mu\text{J}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 9\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	15	-	ns
$t_r$	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	61	-	ns
$t_f$	Fall time		-	16	-	ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		72	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 18\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 100\text{ V}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	360		ns
$Q_{rr}$	Reverse recovery charge		-	5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	$I_{SD} = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 100\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	28		A
$t_{rr}$	Reverse recovery time		-	445		ns
$Q_{rr}$	Reverse recovery charge		-	6.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	29		A

1. Pulse width is limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

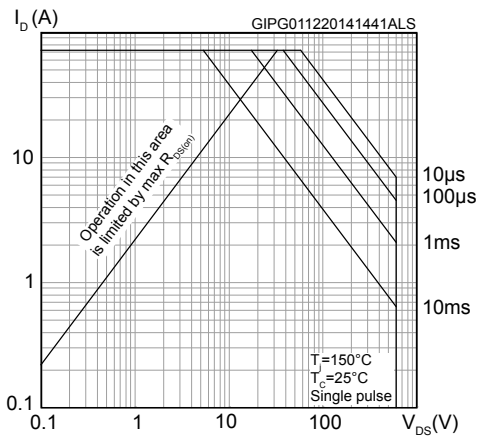


Figure 2. Thermal impedance

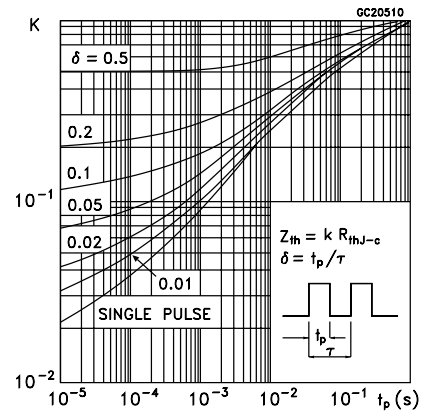


Figure 3. Output characteristics

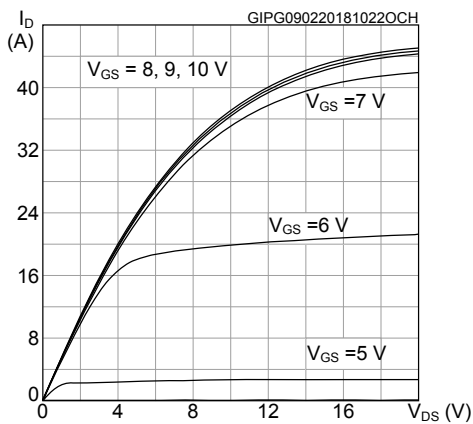


Figure 4. Transfer characteristics

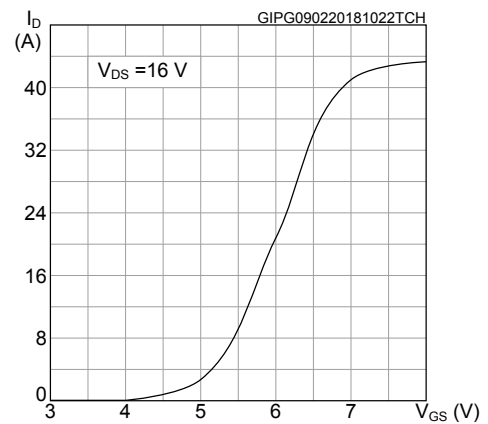


Figure 5. Gate charge vs gate-source voltage

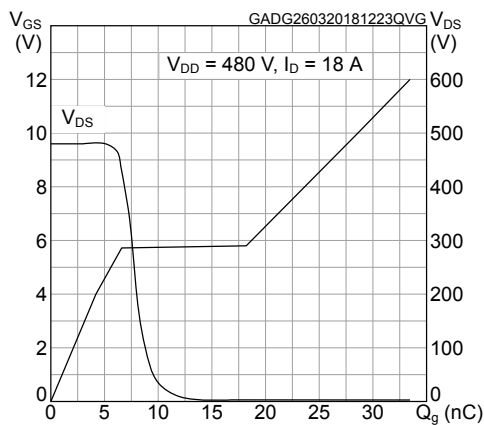
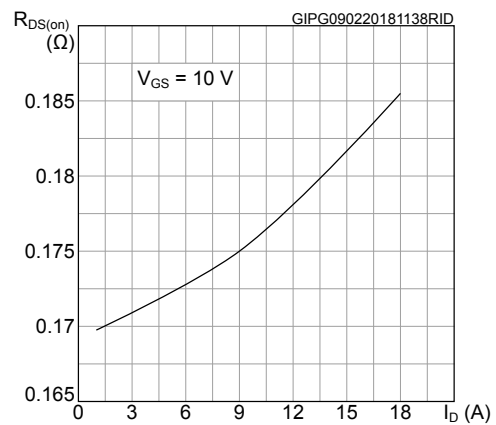
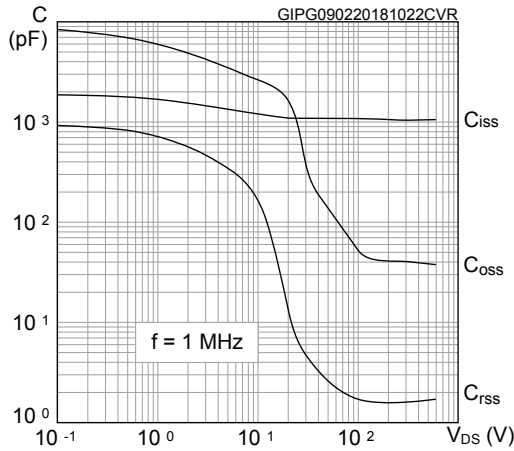


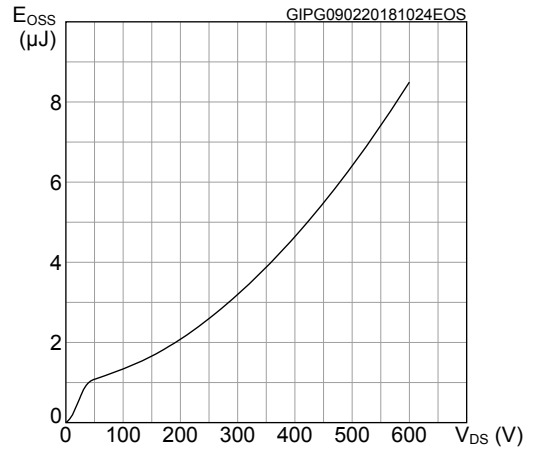
Figure 6. Static drain-source on-resistance



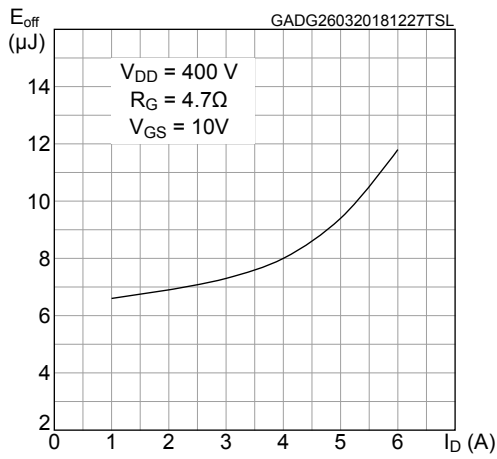
**Figure 7. Capacitance variations**



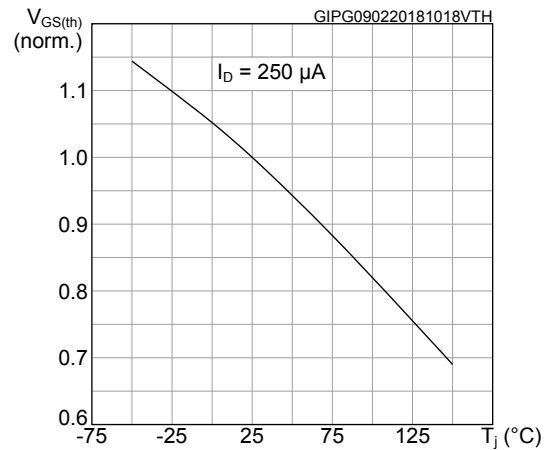
**Figure 8. Output capacitance stored energy**



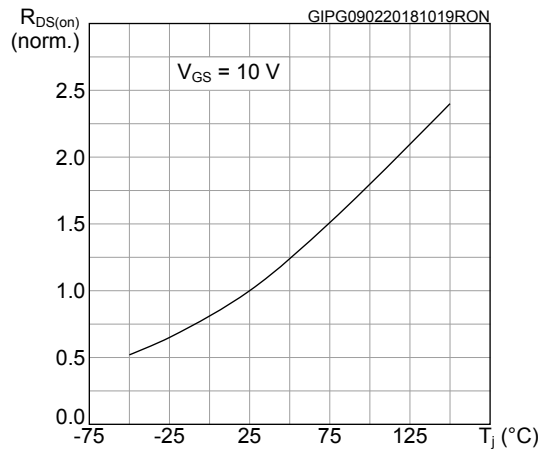
**Figure 9. Turn-off switching energy vs drain current**



**Figure 10. Normalized gate threshold voltage vs temperature**



**Figure 11. Normalized on-resistance vs temperature**



**Figure 12. Normalized  $V_{(BR)DSS}$  vs temperature**

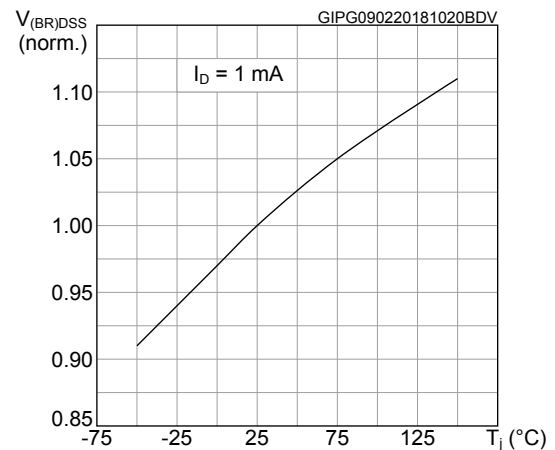
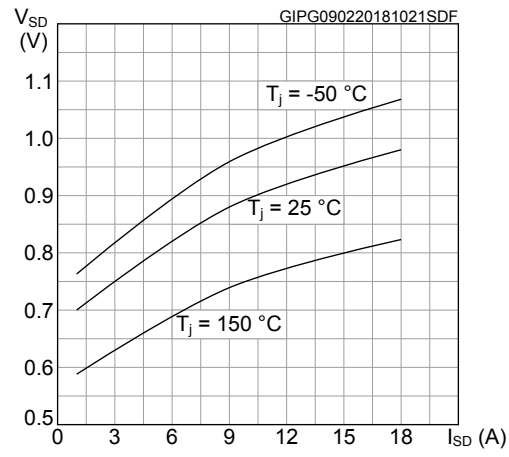
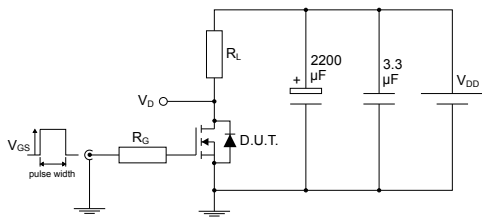


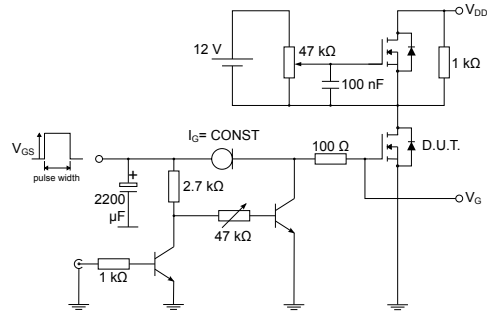
Figure 13. Source-drain diode forward characteristics



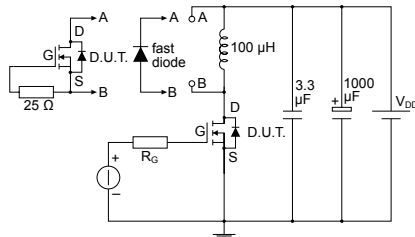
### 3 Test circuits

**Figure 14. Test circuit for resistive load switching times**


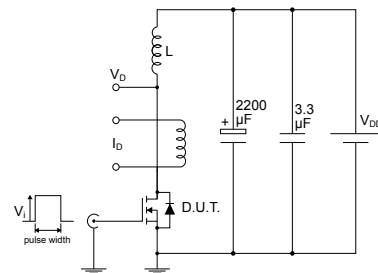
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**Figure 15. Test circuit for gate charge behavior**


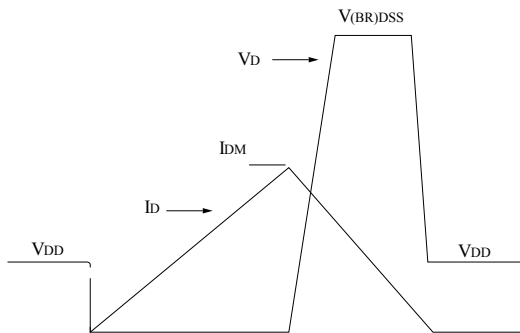
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**Figure 16. Test circuit for inductive load switching and diode recovery times**


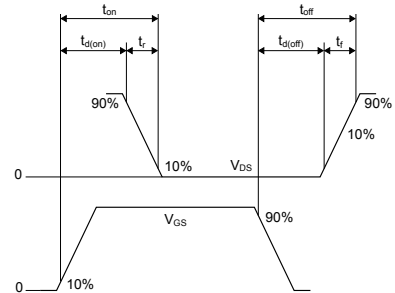
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**Figure 17. Unclamped inductive load test circuit**


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**Figure 18. Unclamped inductive waveform**


AM01472v1

**Figure 19. Switching time waveform**


AM01473v1



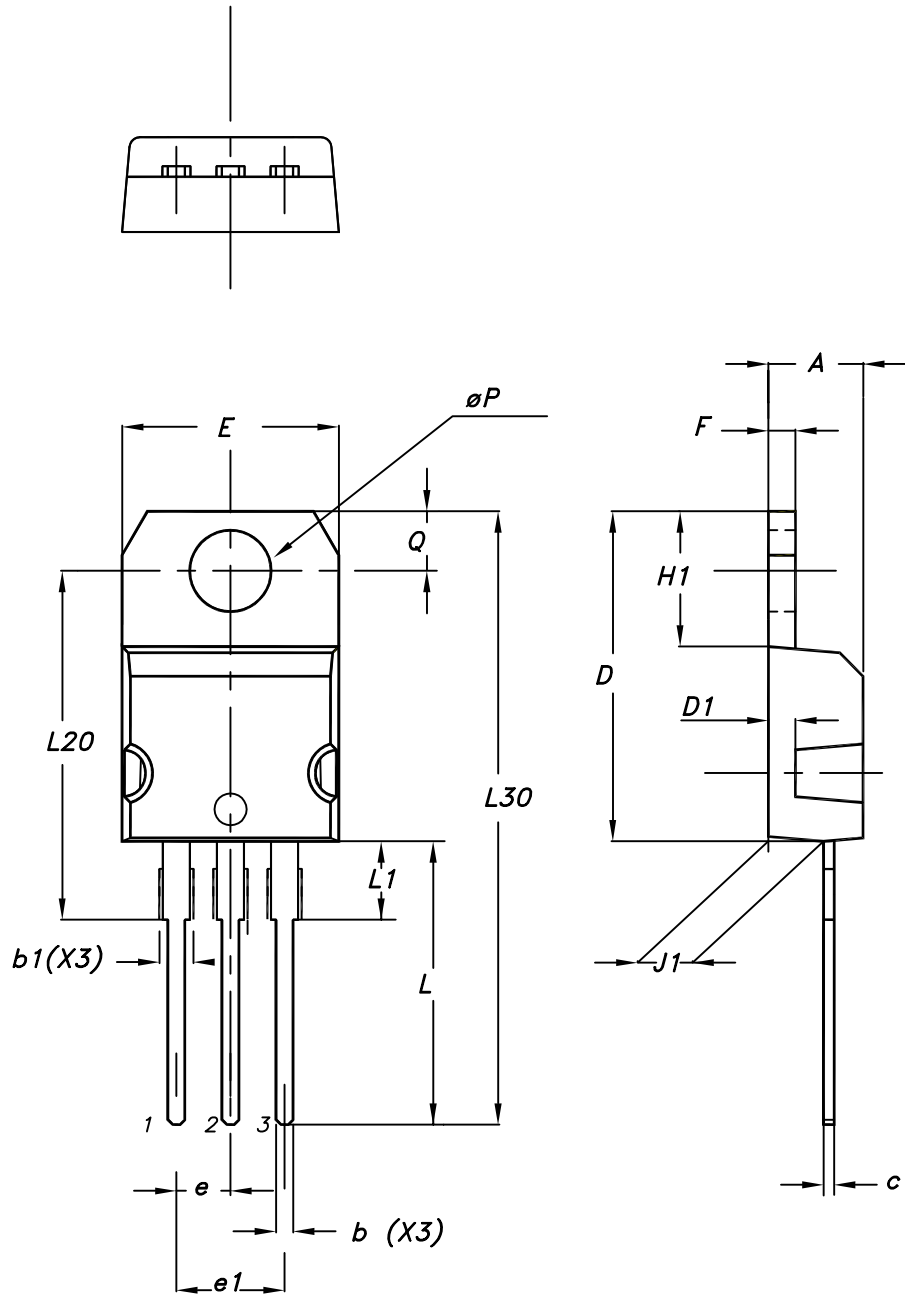
## 4 Package information

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In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

## 4.1 TO-220 type A package information

Figure 20. TO-220 type A package outline



0015988\_typeA\_Rev\_21

**Table 9. TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

## Revision history

**Table 10. Document revision history**

Date	Revision	Changes
01-Dec-2014	1	First release.
12-Jan-2015	2	Updated product status from "preliminary data" to "production data".
13-Feb-2018	3	<p>Removed maturity status indication from cover page.</p> <p>Modified schematic on cover page.</p> <p>Modified <i>Table 1. Absolute maximum ratings</i>, <i>Table 4. On/off states</i>, <i>Table 5. Dynamic</i>, <i>Table 6. Switching energy</i>, <i>Table 7. Switching times</i> and <i>Table 8. Source drain diode</i>.</p> <p>Updated <i>Section 2.1 Electrical characteristics (curves)</i>.</p> <p>Minor text changes.</p>
28-May-2018	4	<p>Updated <a href="#">Table 1. Absolute maximum ratings</a>.</p> <p>Updated <a href="#">Section 2 Electrical characteristics</a> and <a href="#">Section 2.1 Electrical characteristics (curves)</a>.</p> <p>Minor text changes</p>

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